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Thyristor High Voltage, Phase Control SCR, 70 A



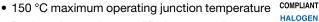
LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{T(AV)} 70 A					
V _{DRM} /V _{RRM}	1200 V, 1600 V				
V _{TM}	1.40 V				
I _{GT}	100 mA				
T _J	-40 °C to 150 °C				
Circuit configuration	Single SCR				
Package	Super TO-247				

FEATURES

- · High surge capability
- · High voltage input rectification



FREE

- Designed and qualified according
- JEDEC®-JESD 47
- Halogen-free
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- AC switches
- · High voltage input rectification (soft start)
- · High current crow-bar
- · Other phase-control circuits
- · Designed to be used with Vishay input diodes, switches, and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-70TPS..-M3 high voltage series of silicon controlled rectifiers are specifically designed for high and medium power switching, and phase control applications.

MECHANICAL DATA

Case: Super TO-247

Molding compound meets UL 94 V-0 flammability rating Terminal: matte tin plated leads, solderable per J-STD-002

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	70	۸				
I _{RMS}	Lead current limitation	75	Α				
V _{RRM} /V _{DRM}	Range	1200 to 1600	V				
I _{TSM}		930	A				
V_{TM}	100 A, T _J = 25 °C	1.40	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		-40 to +150	°C				

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 150 °C mA						
VS-70TPS12-M3	1200	1300	42						
VS-70TPS16-M3	1600	1700	42						



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ABSOLUTE MAXIMUM RATINGS					ı	ı
PARAMETER	SYMBOL	TI	EST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	$T_C = 109 ^{\circ}C, 180^{\circ} co$	nduction half sine wav	е	70	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}	Lead current limitation	on		75	Α
Maximum peak, one-cycle	l	10 ms sine pulse, rat	ed V _{RRM} applied		780	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no	voltage reapplied		930	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rat	ed V _{RRM} applied	Initial T _J = T _J maximum	3060	A ² s
waxiinum i-t for fusing	I~L	10 ms sine pulse, no	voltage reapplied	maximam	4325	A-5
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied			43250	A²√s
Low level value of threshold voltage	V _{T(TO)1}				0.95	V
High level value of threshold voltage	V _{T(TO)2}	T = 150 °C		1.05	\ \ \	
Low level value of on-state slope resistance	r _{t1}	T _J = 150 °C		4.15	mΩ	
High level value of on-state slope resistance	r _{t2}				3.65	11152
Maximum peak on-state voltage	V_{TM}	100 A, T _J = 25 °C			1.4	V
Maximum rate of rise of turned-on current	dl/dt	T _J = 25 °C		150	A/µs	
Maximum holding current	I _H	Anode supply = 6 V, resistive load, initial I _T = 1 A, T _J = 25 °C		250		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		400	A	
Marian and disease last and a summer	1 /1	T _J = 25 °C	V_{R} = rated V_{RRM}/V_{DR}	M	1.0	mA
Maximum reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 150 °C	$(T_J = T_J \text{ max., linear})$		42	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = 150 ^{\circ}\text{C}$ $V_{DRM} = R_g - k = \text{Open}$		500	V/µs	

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}	T = 30 µs		10	W	
Maximum average gate power	P _{G(AV)}	1 = 30 μs		2.5	VV	
Maximum peak gate current	I _{GM}			2.5	Α	
Maximum peak negative gate voltage	-V _{GM}			10		
		T _J = - 40 °C		1.8	V	
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	1.5	V	
		T _J = 150 °C		1.0		
		T _J = - 40 °C		150		
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	100	mA	
		T _J = 150 °C		65		
Maximum DC gate voltage not to trigger	V_{GD}	T 450 % V		0.14	V	
Maximum DC gate current not to trigger	I _{GD}	$T_J = 150 ^{\circ}\text{C}, V_{DRM} = \text{rated value}$ 3.0			mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t _{gt}	I_R = 70 A, V_D = 50 % V_{DRM} , I_{gt} = 300 mA, T_J = 25 °C	2	-	
Turn-off time	t _q	$\begin{array}{l} I_{R} = 70 \text{ A, V}_{D} = 80 \text{ \% V}_{DRM} \text{, dV/dt} = 20 \text{ V/}\mu\text{s, t}_{p} = 200 \mu\text{s} \\ I_{gt} = 100 \text{ mA, dI/dt} = 10 \text{ A/}\mu\text{s, V}_{R} = 100 \text{ V, T}_{J} = 150 ^{\circ}\text{C} \end{array}$	170	-	μs

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction temperature range		TJ		-40 to +150	°C		
Maximum storage temperature	range	T _{Stg}		-40 to +150			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.27			
Maximum thermal resistance, junction to ambient		R _{thJA}		40	°C/W		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.2			
Approximate weight				6	g		
Mounting torque minimum				6 (5)	kgf · cm		
Mounting torque	maximum			12 (10)	(lbf · in)		
Marking device			Consist de Super TO 247	70TPS	12		
			Case style Super TO-247	70TPS	16		

ΔR_{thJ-hs} Conduction per junction											
DEVICE	S	SINE HALF WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION							UNITS		
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-70TPSM3	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

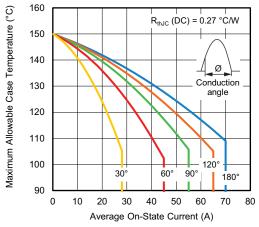


Fig. 1 - Current Rating Characteristics

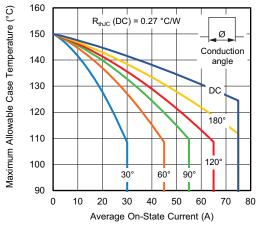


Fig. 2 - Current Rating Characteristics

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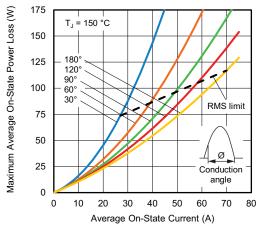


Fig. 3 - On-State Power Loss Characteristics

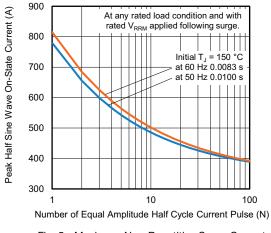


Fig. 5 - Maximum Non-Repetitive Surge Current

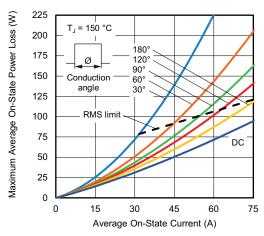


Fig. 4 - On-State Power Loss Characteristic

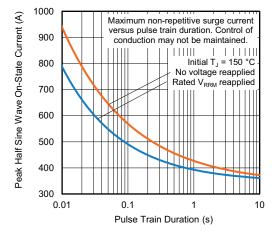


Fig. 6 - Maximum Non-Repetitive Surge Current

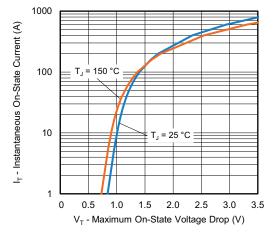


Fig. 7 - On-State Voltage Drop Characteristics

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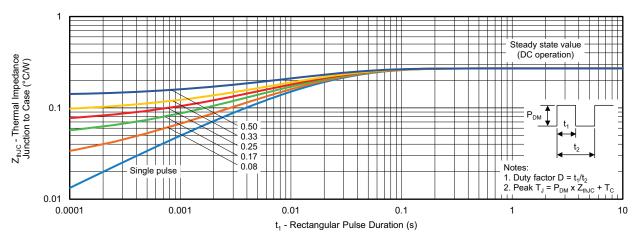
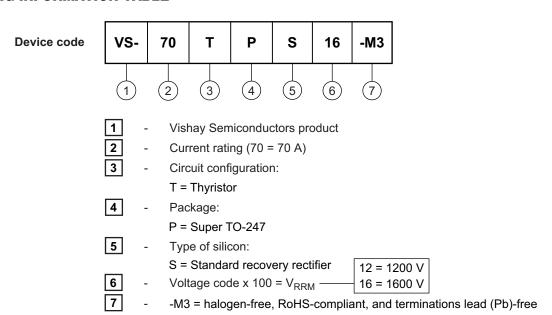


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



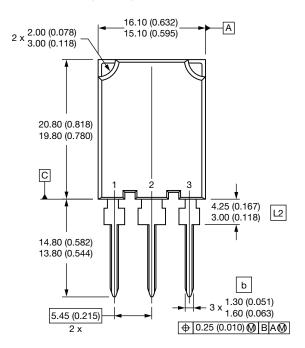
ORDERING INFORMATION (example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-70TPS12-M3	25	500	Antistatic plastic tube						
VS-70TPS16-M3	25	500	Antistatic plastic tube						

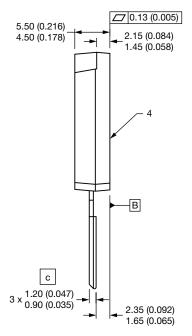
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?97136</u>						
Part marking information	www.vishay.com/doc?95683					

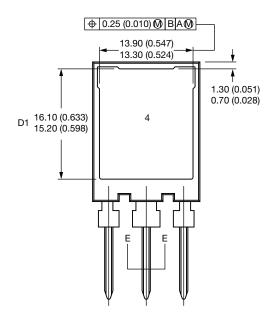
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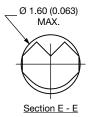
Super TO-247

DIMENSIONS in millimeters (inches)









Lead assignments

SCR

- 1 Cathode
- 2 Anode
- 3 Gate
- 4 Anode

Notes

- (1) Dimension and tolerancing per ASME Y14.5M-1994
- (2) Controlling dimension: millimeter
- ⁽³⁾ Outline conforms to JEDEC® outline TO-274AA, except D1, b min., c min., L2 min.



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